

isc Silicon NPN Darlington Power Transistor

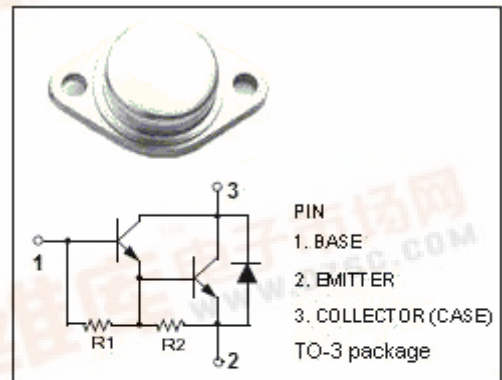
MJ1000

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 60V(\text{Min.})$
- High DC Current Gain-
: $h_{FE} = 1000(\text{Min.}) @ I_C = 3A$
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = 2.0V(\text{Max.}) @ I_C = 3A$

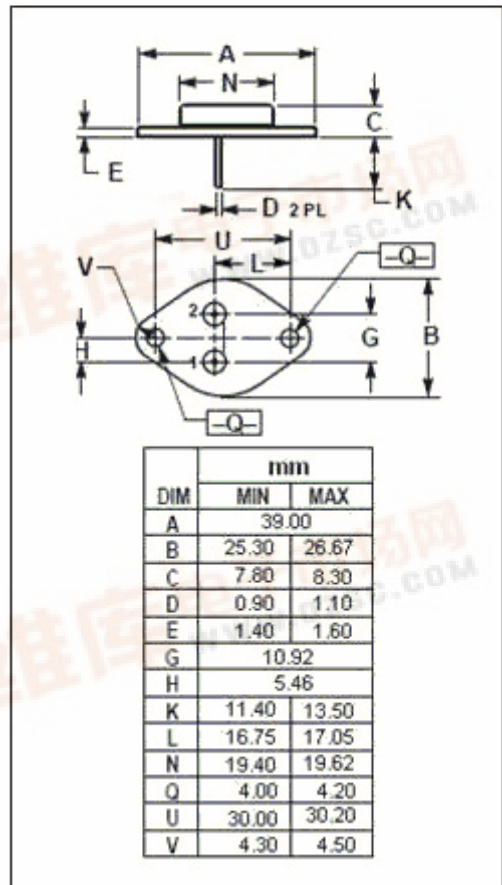
APPLICATIONS

- Designed for use as output devices in complementary general purpose amplifier applications.



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	10	A
I_B	Base Current-Continuous	0.1	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	90	W
T_j	Junction Temperature	200	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~+200	$^\circ\text{C}$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.94	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=0.1\text{A}; I_B=0$	60			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=12\text{mA}$			2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=8\text{A}; I_B=40\text{mA}$			4.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=3\text{A}, V_{CE}=3\text{V}$			2.5	V
I_{CER}	Collector Cutoff Current	$V_{CE}=60\text{V}; R_{BE}=1\text{k}\Omega$ $V_{CE}=60\text{V}; R_{BE}=1\text{k}\Omega; T_C=150^{\circ}\text{C}$			1.0 5.0	mA
I_{CEO}	Collector Cutoff Current	$V_{CE}=30\text{V}; I_B=0$			0.5	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			2.0	mA
h_{FE-1}	DC Current Gain	$I_C=3\text{A}, V_{CE}=3\text{V}$	1000			
h_{FE-2}	DC Current Gain	$I_C=4\text{A}, V_{CE}=3\text{V}$	750			